



浩畅半导体
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BAV16WS/1N4148WS

FAST SWITCHING DIODE

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客户确认：

公司签章：

部门

工程部

品保部

采购部

签名

日期



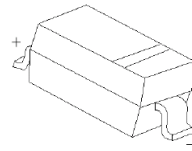
BAV16WS/1N4148WS

FAST SWITCHING DIODE

FEATURES

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- High Conductance

SOD-323



MARKING: T6, T4

Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	71	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	150	mA
Peak Forward Surge Current @t=1.0μs	I_{FSM}	2.0	A
@t=1.0s		1.0	
Power Dissipation	P_d	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V_{F1}			0.715	V	$I_F=1mA$
	V_{F2}			0.855	V	$I_F=10mA$
	V_{F3}			1.0	V	$I_F=50mA$
	V_{F4}			1.25	V	$I_F=150mA$
Reverse current	I_{R1}			1	μA	$V_R=75V$
	I_{R2}			25	nA	$V_R=20V$
Capacitance between terminals	C_T			2	pF	$V_R=0V, f=1MHz$
Reverse recovery time	t_{rr}			4	ns	$I_F=I_R=10mA$ $I_{rr}=0.1I_R, R_L=100\Omega$

1N4148WS

Typical Characteristics

